

GaAs-IR-Lumineszenzdioden
GaAs Infrared Emitters
Lead (Pb) Free Product - RoHS Compliant

SFH 415



Wesentliche Merkmale

- GaAs-LED mit sehr hohem Wirkungsgrad
- Hohe Zuverlässigkeit
- UL Version erhältlich
- Gute spektrale Anpassung an Si-Fotoempfänger
- SFH 415: Gehäusegleich mit SFH 300, SFH 203

Features

- Very highly efficient GaAs-LED
- High reliability
- UL version available
- Spectral match with silicon photodetectors
- SFH 415: Same package as SFH 300, SFH 203

Anwendungen

- IR-Fernsteuerung von Fernseh- und Rundfunkgeräten, Videorecordern, Lichtdimmern
- Gerätefernsteuerungen für Gleich- und Wechsellichtbetrieb
- Rauchmelder
- Sensorik
- Diskrete Lichtschranken

Applications

- IR remote control of hi-fi and TV-sets, video tape recorders, dimmers
- Remote control for steady and varying intensity
- Smoke detectors
- Sensor technology
- Discrete interrupters

| Typ Type | Bestellnummer Ordering Code | Strahlstärkegruppierung ¹⁾ ($I_F = 100 \text{ mA}$, $t_p = 20 \text{ ms}$) Radiant Intensity Grouping ¹⁾ I_e (mW/sr) |
|-------------|--------------------------------|---|
| SFH 415 | Q62702-P0296 | > 25 |
| SFH 415-U | Q62702-P1137 | > 40 |

¹⁾ gemessen bei einem Raumwinkel $\Omega = 0.01 \text{ sr}$ / measured at a solid angle of $\Omega = 0.01 \text{ sr}$

Grenzwerte ($T_A = 25\text{ °C}$)**Maximum Ratings**

| Bezeichnung Parameter | Symbol Symbol | Wert Value | Einheit Unit |
|--|-------------------|----------------|-----------------|
| Betriebs- und Lagertemperatur Operating and storage temperature range | $T_{op}; T_{stg}$ | - 40 ... + 100 | °C |
| Sperrspannung Reverse voltage | V_R | 5 | V |
| Durchlassstrom Forward current | I_F | 100 | mA |
| Stoßstrom, $t_p = 10\ \mu\text{s}$, $D = 0$ Surge current | I_{FSM} | 3 | A |
| Verlustleistung Power dissipation | P_{tot} | 165 | mW |
| Wärmewiderstand Thermal resistance | R_{thJA} | 450 | K/W |

Kennwerte ($T_A = 25\text{ °C}$)**Characteristics**

| Bezeichnung Parameter | Symbol Symbol | Wert Value | Einheit Unit |
|---|------------------------------|------------------|-----------------|
| Wellenlänge der Strahlung Wavelength at peak emission $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$ | λ_{peak} | 950 | nm |
| Spektrale Bandbreite bei 50% von I_{max} Spectral bandwidth at 50% of I_{max} $I_F = 100\text{ mA}$ | $\Delta\lambda$ | 55 | nm |
| Abstrahlwinkel Half angle SFH 415 | φ | ± 17 | Grad |
| Aktive Chipfläche Active chip area | A | 0.09 | mm ² |
| Abmessungen der aktiven Chipfläche Dimensions of the active chip area | $L \times B$ $L \times W$ | 0.3×0.3 | mm ² |
| Abstand Chipoberfläche bis Linsenscheitel Distance chip front to lens top | H | 4.2 ... 4.8 | mm |

Kennwerte ($T_A = 25\text{ °C}$)

Characteristics (cont'd)

| Bezeichnung Parameter | Symbol Symbol | Wert Value | Einheit Unit |
|---|------------------|--|-----------------|
| Schaltzeiten, I_e von 10% auf 90% und von 90% auf 10%, bei $I_F = 100\text{ mA}$, $R_L = 50\ \Omega$ Switching times, I_e from 10% to 90% and from 90% to 10%, $I_F = 100\text{ mA}$, $R_L = 50\ \Omega$ | t_r, t_f | 0.5 | μs |
| Kapazität Capacitance $V_R = 0\text{ V}$, $f = 1\text{ MHz}$ | C_o | 25 | pF |
| Durchlassspannung Forward voltage $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$ $I_F = 1\text{ A}$, $t_p = 100\ \mu\text{s}$ | V_F V_F | 1.3 (≤ 1.5) 2.3 (≤ 2.8) | V V |
| Sperrstrom Reverse current $V_R = 5\text{ V}$ | I_R | 0.01 (≤ 1) | μA |
| Gesamtstrahlungsfluss Total radiant flux $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$ | Φ_e | 22 | mW |
| Temperaturkoeffizient von I_e bzw. Φ_e , $I_F = 100\text{ mA}$ Temperature coefficient of I_e or Φ_e , $I_F = 100\text{ mA}$ | TC_I | - 0.5 | %/K |
| Temperaturkoeffizient von V_F , $I_F = 100\text{ mA}$ Temperature coefficient of V_F , $I_F = 100\text{ mA}$ | TC_V | - 2 | mV/K |
| Temperaturkoeffizient von λ , $I_F = 100\text{ mA}$ Temperature coefficient of λ , $I_F = 100\text{ mA}$ | TC_λ | + 0.3 | nm/K |

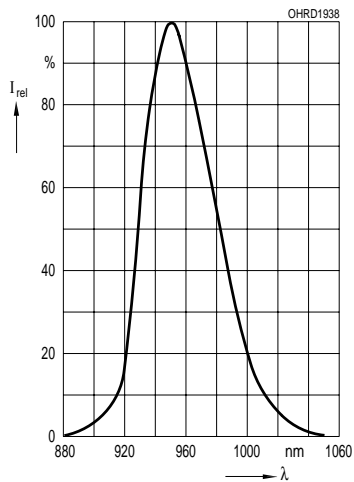
Gruppierung der Strahlstärke I_e in Achsrichtunggemessen bei einem Raumwinkel $\Omega = 0.01$ sr**Grouping of Radiant Intensity I_e in Axial Direction**at a solid angle of $\Omega = 0.01$ sr

| Bezeichnung Parameter | Symbol | Wert Value | | | Einheit Unit |
|--|--|---------------|-------------------------|-----------|-----------------|
| | | SFH 415 | SFH 415-T ¹⁾ | SFH 415-U | |
| Strahlstärke Radiant intensity $I_F = 100$ mA, $t_p = 20$ ms | $I_{e \text{ min}}$ $I_{e \text{ max}}$ | 25 – | 25 50 | 40 – | mW/sr mW/sr |
| Strahlstärke Radiant intensity $I_F = 1$ A, $t_p = 100$ μ s | $I_{e \text{ typ.}}$ | – | 350 | 450 | mW/sr |

¹⁾ SFH 415-T kann nicht einzeln bestellt werden. / SFH 415-T can not be ordered separately.

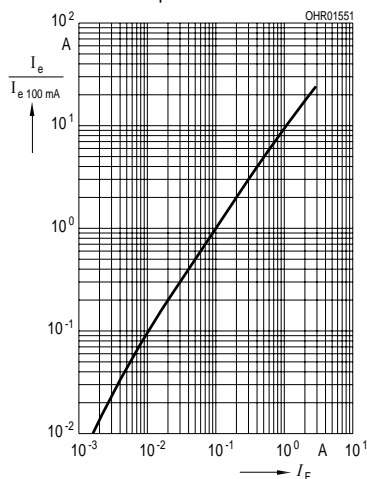
Relative Spectral Emission

$I_{rel} = f(\lambda)$



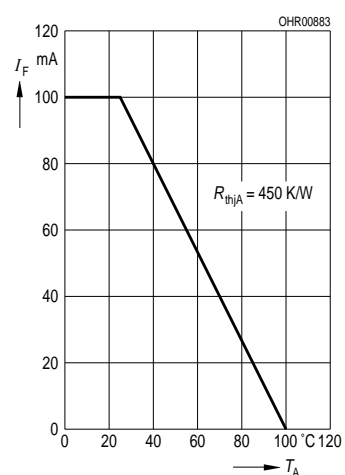
Radiant Intensity $\frac{I_e}{I_e 100 \text{ mA}} = f(I_F)$

Single pulse, $t_p = 20 \mu\text{s}$



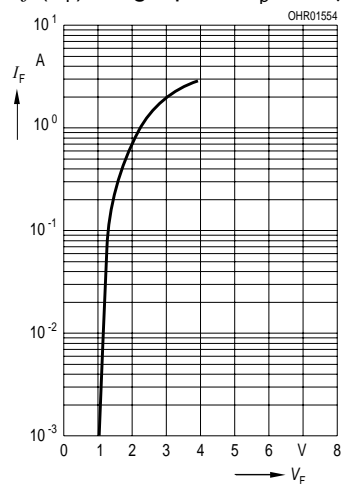
Max. Permissible Forward Current

$I_F = f(T_A)$



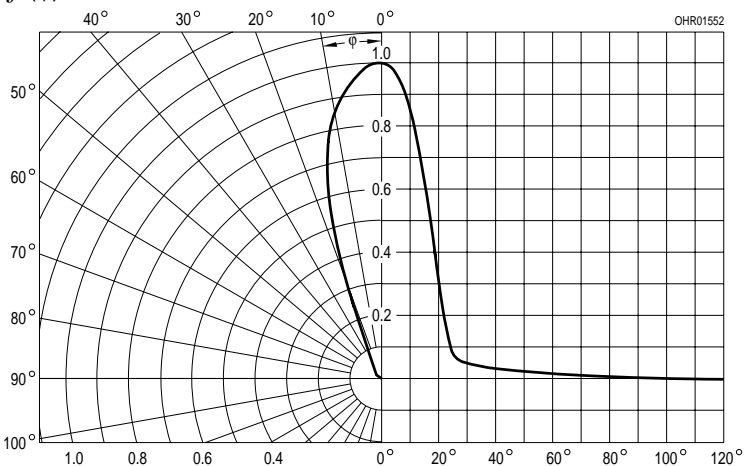
Forward Current

$I_F = f(V_F)$, single pulse, $t_p = 20 \mu\text{s}$



Radiation Characteristics,

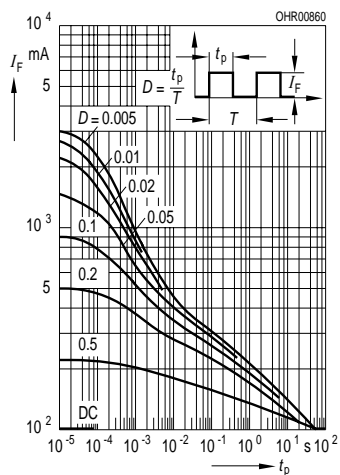
$I_{rel} = f(\varphi)$



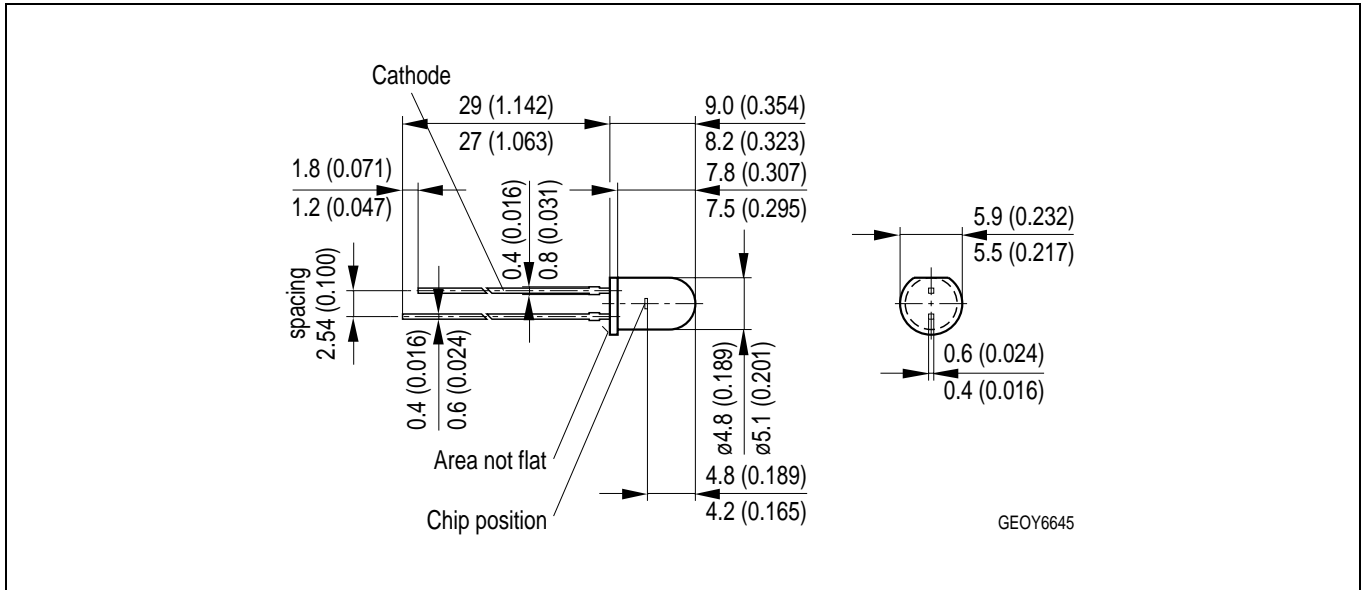
Permissible Pulse Handling Capability

$I_F = f(\tau)$, $T_A = 25 \text{ }^\circ\text{C}$

duty cycle $D =$ parameter



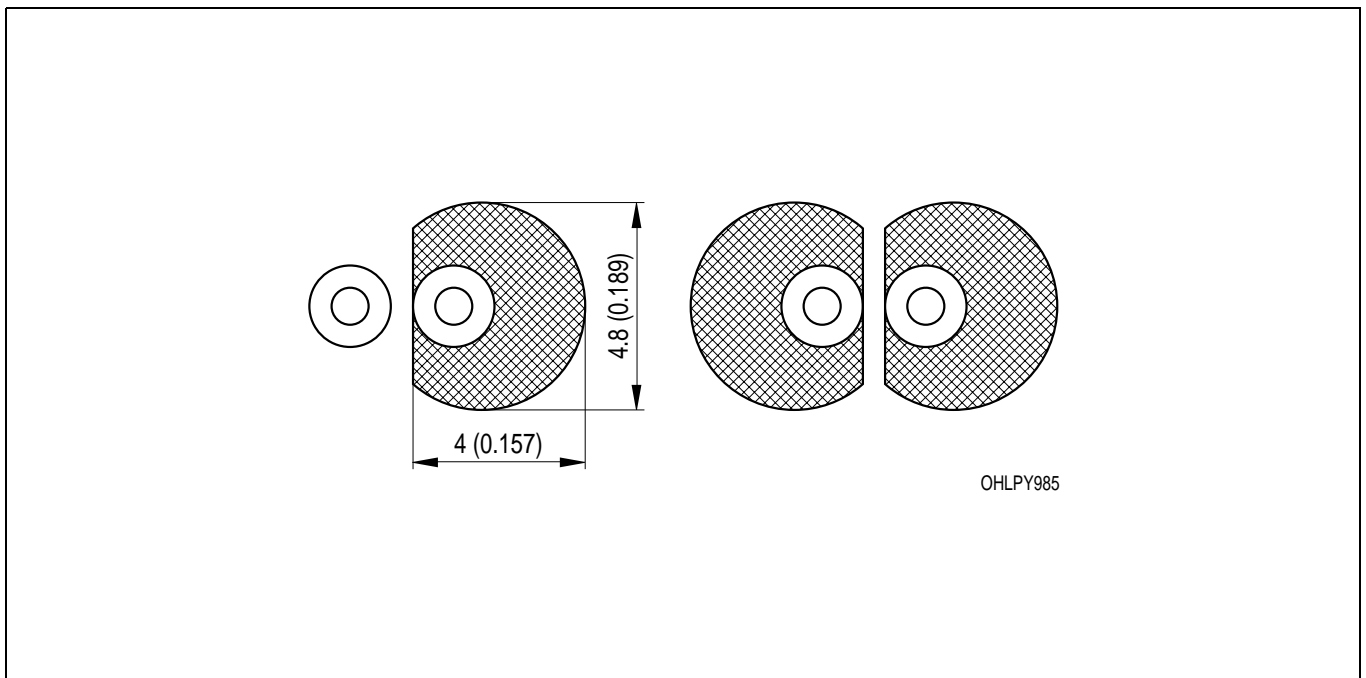
**Maßzeichnung
Package Outlines**



Maße in mm (inch) / Dimensions in mm (inch).

**Empfohlenes Lötpadesign
Recommended Solder Pad**

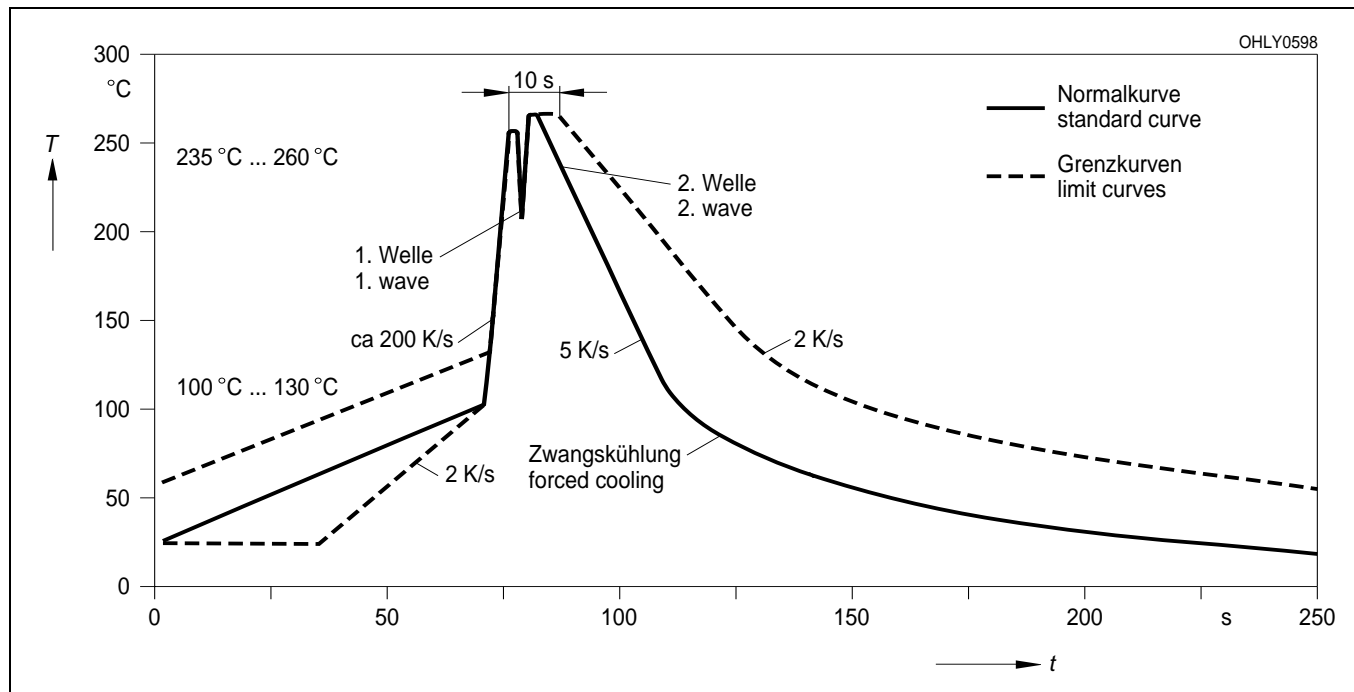
**Wellenlöten (TTW)
TTW Soldering**



Maße in mm (inch) / Dimensions in mm (inch).

Lötbedingungen
Soldering Conditions
Wellenlöten (TTW)
TTW Soldering

(nach CECC 00802)
(acc. to CECC 00802)



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